

## N and P-Channel Enhancement Mode Power MOSFET

### Description

The NCE4606 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. The complementary MOSFETs may be used to form a level shifted high side switch, and for a host of other applications.

### General Features

#### ● N-Channel

$$V_{DS} = 30V, I_D = 6.5A$$

$$R_{DS(ON)} < 24m\Omega @ V_{GS}=10V$$

$$R_{DS(ON)} < 37m\Omega @ V_{GS}=4.5V$$

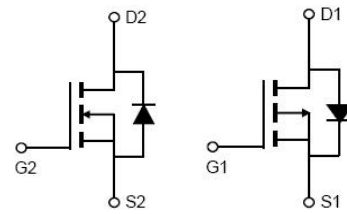
#### ● P-Channel

$$V_{DS} = -30V, I_D = -7A$$

$$R_{DS(ON)} < 32m\Omega @ V_{GS}=-10V$$

$$R_{DS(ON)} < 70m\Omega @ V_{GS}=-4.5V$$

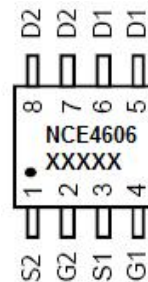
- High power and current handing capability
- Lead free product is acquired
- Surface mount package
- MSL3 up to 260°C peak reflow



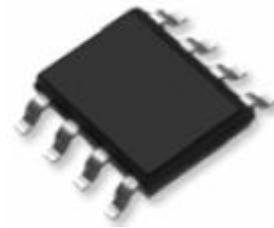
N-channel

P-channel

### Schematic diagram



Marking and pin assignment



SOP-8 top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE4606	NCE4606	SOP-8	Ø330mm	12mm	4000 units

### Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	N-Channel	P-Channel	Unit	
Drain-Source Voltage	$V_{DS}$	30	-30	V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$	$\pm 20$	V	
Continuous Drain Current	$I_D$	$T_A=25^\circ\text{C}$	6.5	-7	A
		$T_A=70^\circ\text{C}$	5.4	-5.8	
Pulsed Drain Current (Note 1)	$I_{DM}$	30	-30	A	
Maximum Power Dissipation	$P_D$	2.0	2.0	W	
Single pulse avalanche energy (Note 6)	$E_{AS}$	39	72	mJ	
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	-55 To 150	$^\circ\text{C}$	

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	N-Ch	62.5	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	P-Ch	62.5	$^\circ\text{C/W}$

**N-CH Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit	
<b>Off Characteristics</b>							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30	33	-	V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	-	1	μA	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA	
<b>On Characteristics (Note 3)</b>							
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1	1.6	2.5	V	
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =6A	T <sub>J</sub> =25°C	-	19	24	mΩ
			T <sub>J</sub> =125°C	-	30	39	
			T <sub>J</sub> =150°C	-	34	44	
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A	T <sub>J</sub> =25°C	-	26	37	mΩ
			T <sub>J</sub> =125°C	-	41	58	
			T <sub>J</sub> =150°C	-	45.5	64	
Gate resistance	R <sub>G</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, F=1.0MHz	-	1.1	-	Ω	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =6A	15	-	-	S	
<b>Dynamic Characteristics (Note 4)</b>							
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, F=1.0MHz	-	530.3	-	PF	
Output Capacitance	C <sub>OSS</sub>		-	67.1	-	PF	
Reverse Transfer Capacitance	C <sub>rSS</sub>		-	61.2	-	PF	
<b>Switching Characteristics (Note 4)</b>							
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =15V, I <sub>D</sub> =6A V <sub>GS</sub> =10V, R <sub>GEN</sub> =3Ω	-	4.5	-	nS	
Turn-on Rise Time	t <sub>r</sub>		-	2.5	-	nS	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	14.5	-	nS	
Turn-Off Fall Time	t <sub>f</sub>		-	3.5	-	nS	
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =15V, I <sub>D</sub> =6A, V <sub>GS</sub> =10V	-	14.2	-	nC	
Gate-Source Charge	Q <sub>gs</sub>		-	1.8	-	nC	
Gate-Drain Charge	Q <sub>gd</sub>		-	3.3	-	nC	
<b>Drain-Source Diode Characteristics</b>							
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =6A	-	0.8	1.2	V	
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	6.5	A	
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = I <sub>S</sub>	-	10	-	nS	
Reverse Recovery Charge	Q <sub>rr</sub>	di/dt = 100A/μs (Note 3)	-	5	-	nC	

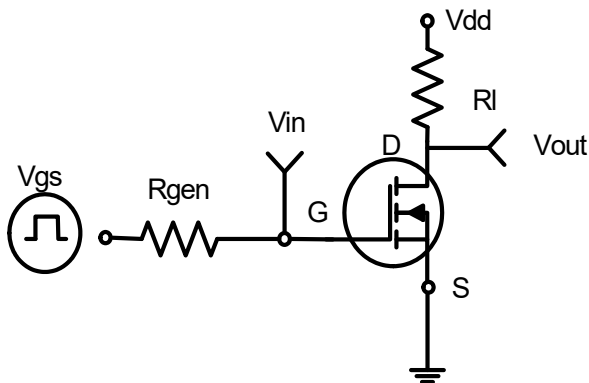
**P-CH Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit	
<b>Off Characteristics</b>							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-30	-33	-	V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	-	-	-1	μA	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA	
<b>On Characteristics (Note 3)</b>							
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1.3	-1.65	-2.5	V	
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-6.5A	T <sub>J</sub> =25°C	-	28	32	mΩ
			T <sub>J</sub> =125°C	-	41	48	
			T <sub>J</sub> =150°C	-	45	52	
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-6.5A	T <sub>J</sub> =25°C	-	49	70	mΩ
			T <sub>J</sub> =125°C	-	63	89	
			T <sub>J</sub> =150°C	-	67.5	96	
Gate resistance	R <sub>G</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, F=1.0MHz	-	4.2	-	Ω	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =-6.5A	10	-	-	S	
<b>Dynamic Characteristics (Note4)</b>							
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, F=1.0MHz	-	729.4	-	PF	
Output Capacitance	C <sub>oss</sub>		-	112.6	-	PF	
Reverse Transfer Capacitance	C <sub>riss</sub>		-	107.5	-	PF	
<b>Switching Characteristics (Note 4)</b>							
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-15V, I <sub>D</sub> =-6.5A V <sub>GS</sub> =-10V, R <sub>GEN</sub> =6Ω	-	7.5	-	nS	
Turn-on Rise Time	t <sub>r</sub>		-	5.5	-	nS	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	19	-	nS	
Turn-Off Fall Time	t <sub>f</sub>		-	7	-	nS	
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-15V, I <sub>D</sub> =-6.5A V <sub>GS</sub> =-10V	-	16.6	-	nC	
Gate-Source Charge	Q <sub>gs</sub>		-	1.8	-	nC	
Gate-Drain Charge	Q <sub>gd</sub>		-	4.2	-	nC	
<b>Drain-Source Diode Characteristics</b>							
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-6.5A	-	-	-1.2	V	
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	-7	A	
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = I <sub>S</sub> di/dt = 100A/μs (Note3)	-	15	-	nS	
Reverse Recovery Charge	Q <sub>rr</sub>		-	10	-	nC	

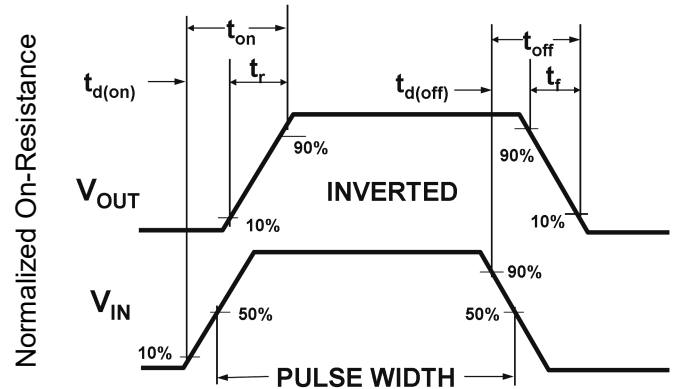
**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

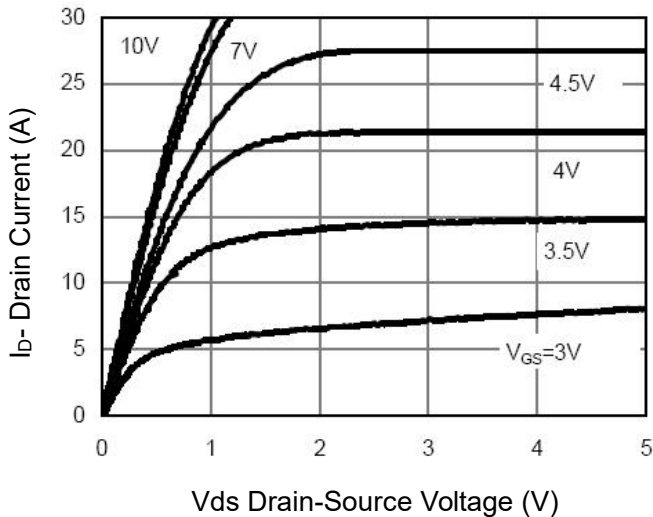
**N- Channel Typical Electrical and Thermal Characteristics (Curves)**



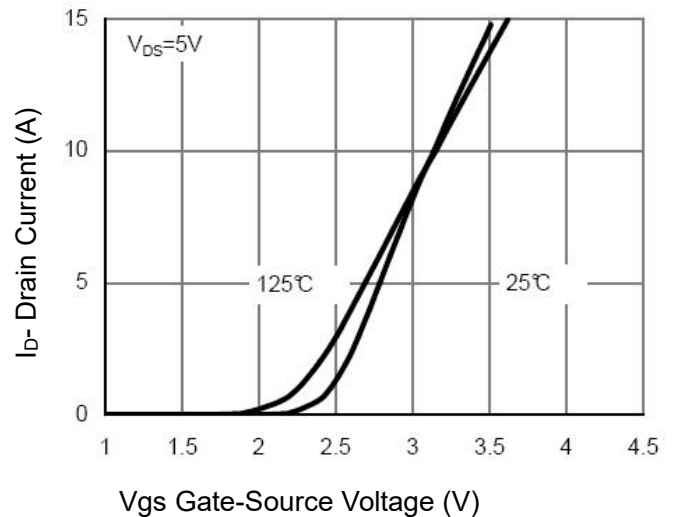
**Figure 1: Switching Test Circuit**



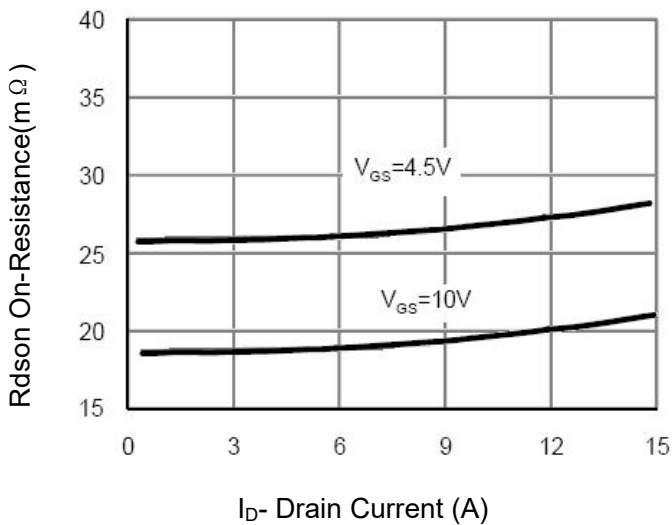
**Figure 2: Switching Waveforms**



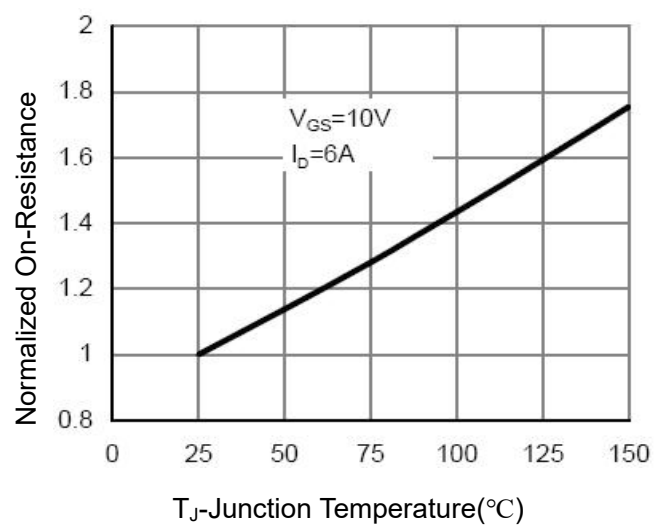
**Figure 3 Output Characteristics**



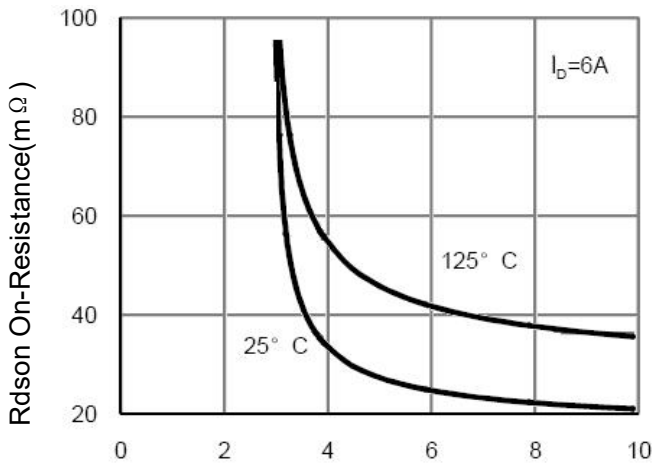
**Figure 4 Transfer Characteristics**



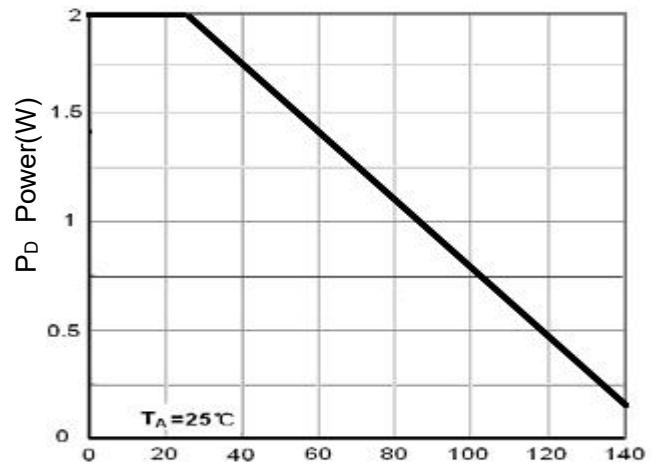
**Figure 5 Drain-Source On-Resistance**



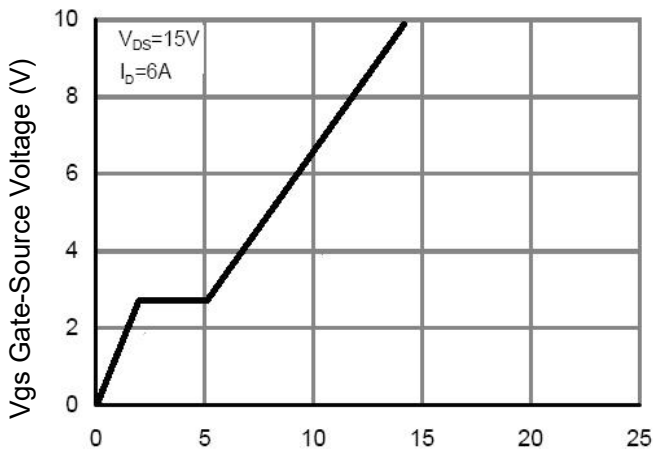
**Figure 6 Drain-Source On-Resistance**



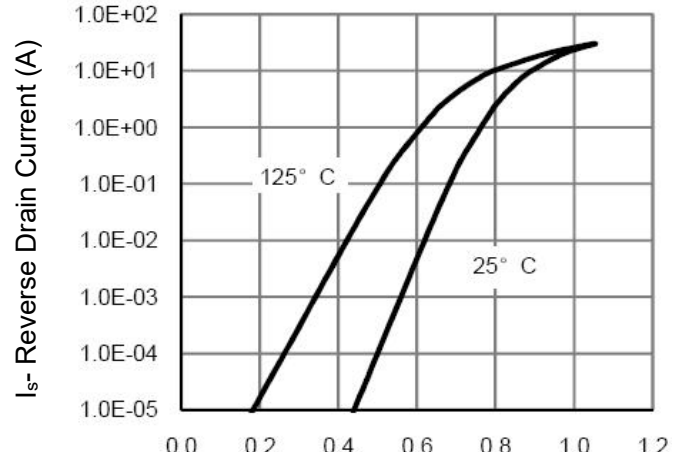
Vgs Gate-Source Voltage (V)  
**Figure 7 Rdson vs Vgs**



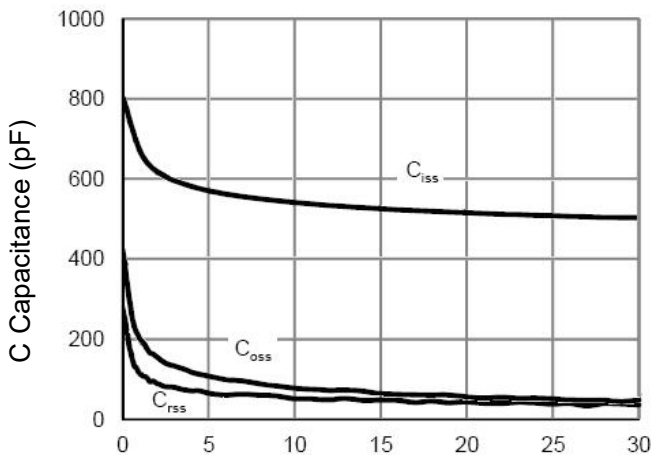
Tj Junction Temperature (°C)  
**Figure 8 Power Dissipation**



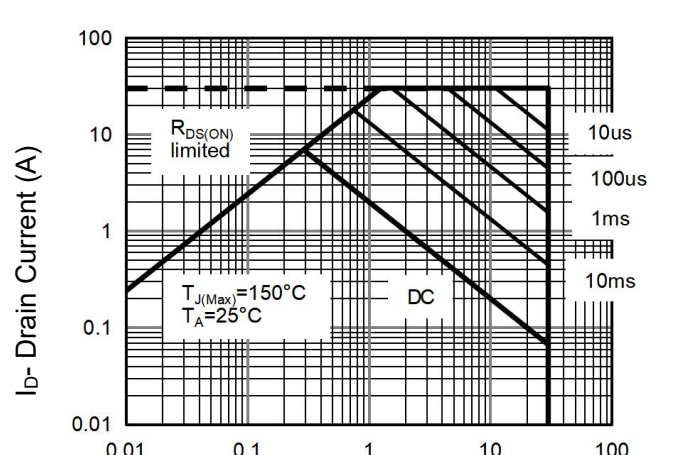
Qg Gate Charge (nC)  
**Figure 9 Gate Charge**



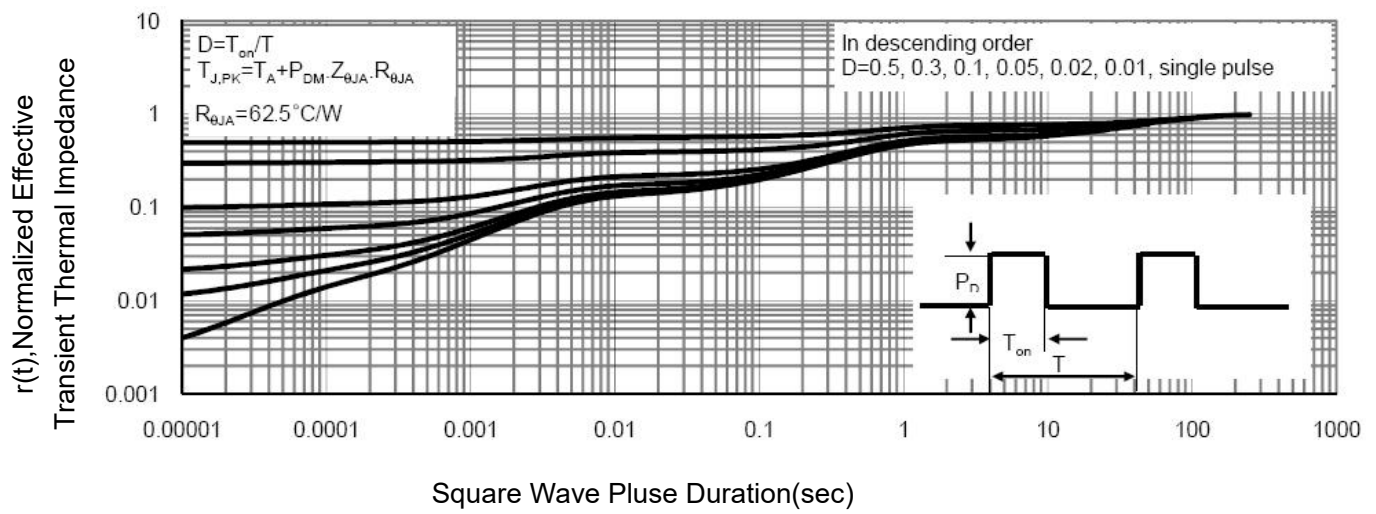
Vds Drain-Source Voltage (V)  
**Figure 10 Source-Drain Diode Forward**



Vds Drain-Source Voltage (V)  
**Figure 11 Capacitance vs Vds**

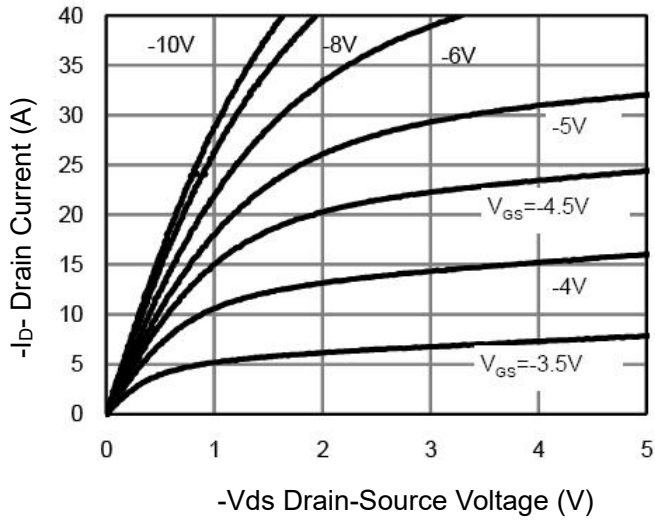


ds Drain-Source Voltage (V)  
**Figure 12 Safe Operation Area**

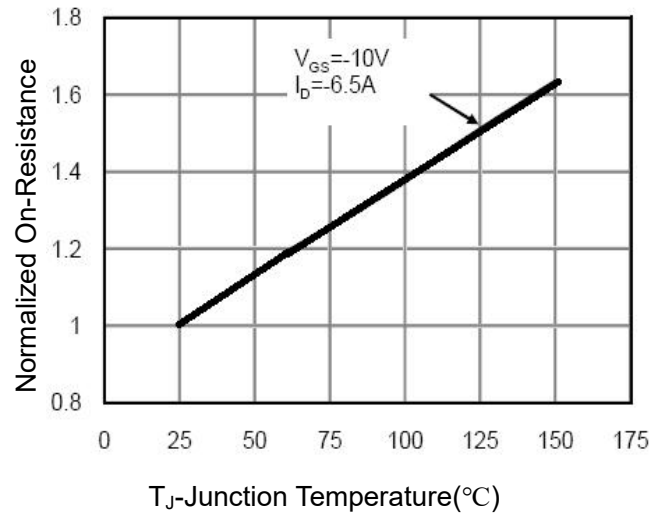


**Figure 13 Normalized Maximum Transient Thermal Impedance**

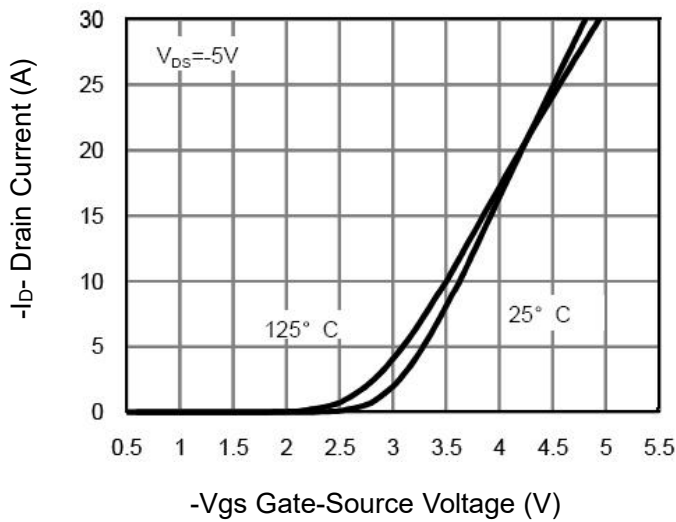
**P- Channel Typical Electrical and Thermal Characteristics (Curves)**



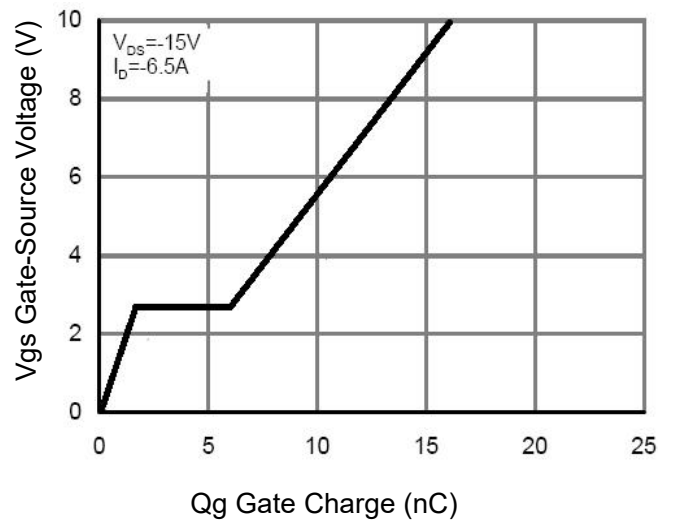
**Figure 1 Output Characteristics**



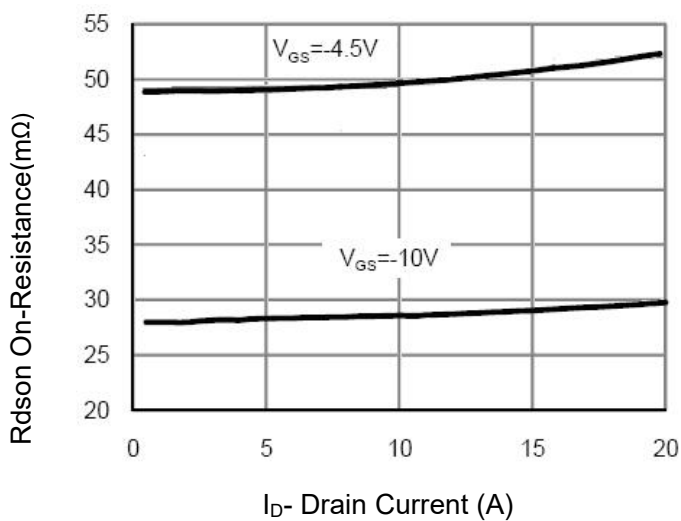
**Figure 4 R<sub>DS(on)</sub>-Junction Temperature**



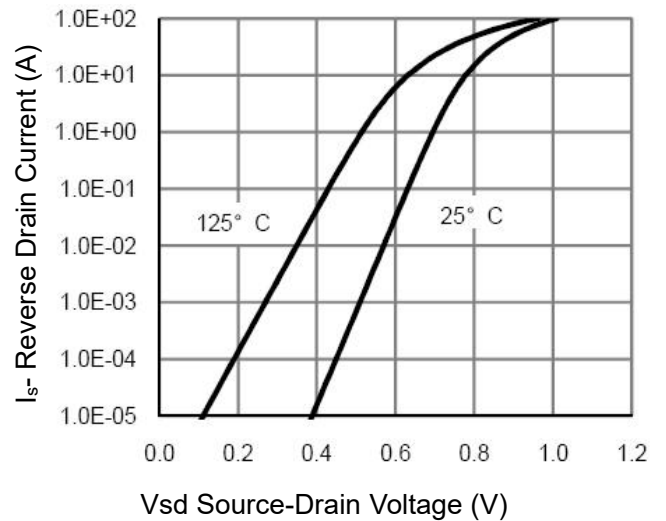
**Figure 2 Transfer Characteristics**



**Figure 5 Gate Charge**



**Figure 3 R<sub>DS(on)</sub>- Drain Current**



**Figure 6 Source- Drain Diode Forward**



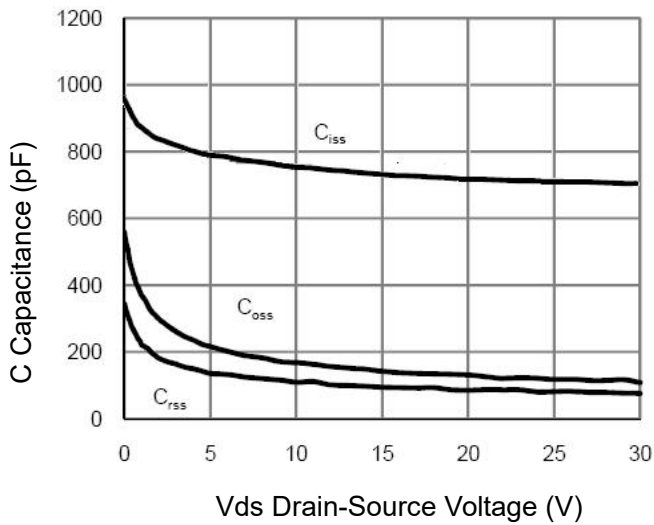


Figure 7 Capacitance vs Vds

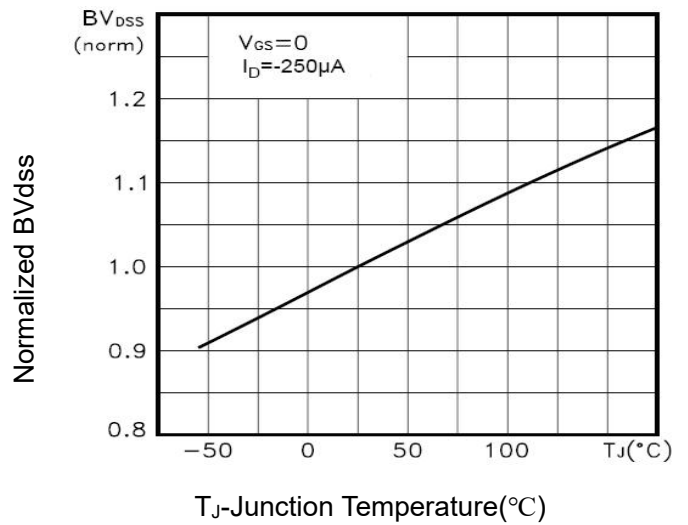


Figure 9 BV<sub>DSS</sub> vs Junction Temperature

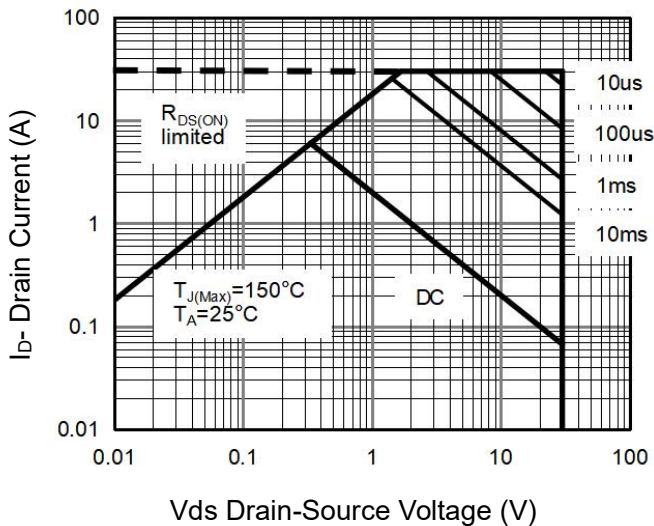


Figure 8 Safe Operation Area

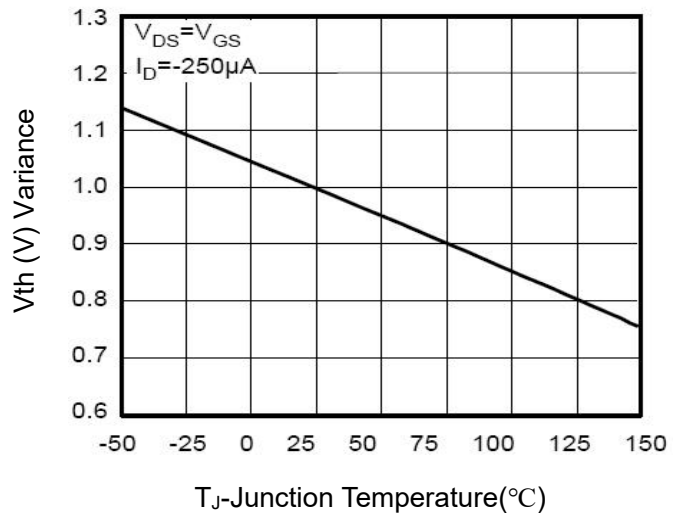


Figure 10 V<sub>GS(th)</sub> vs Junction Temperature

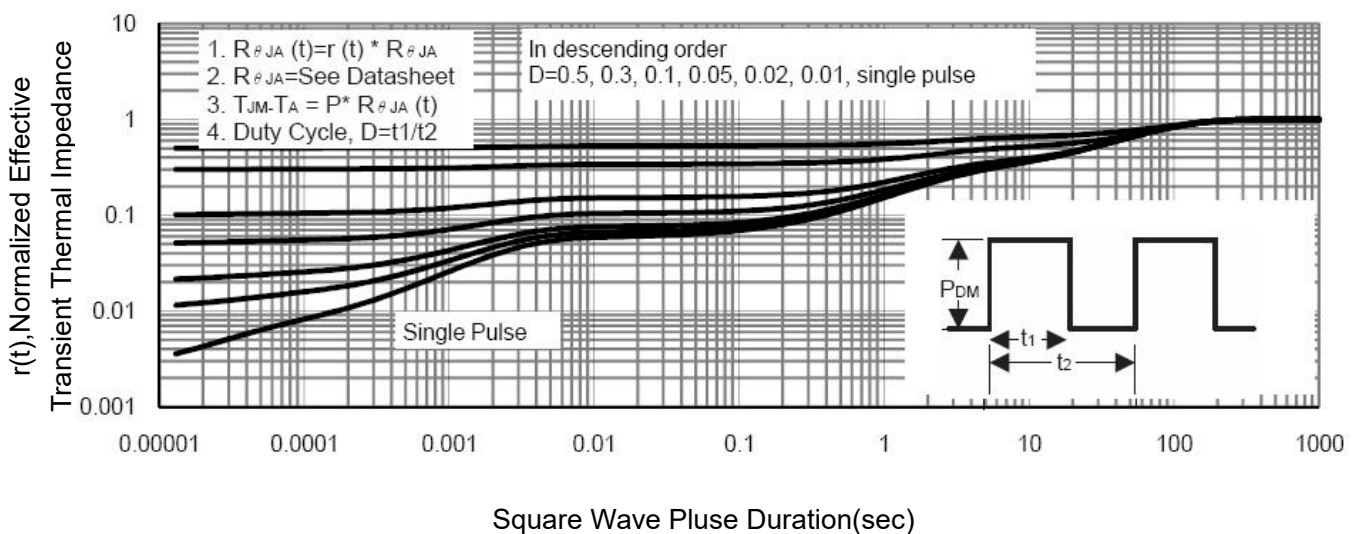
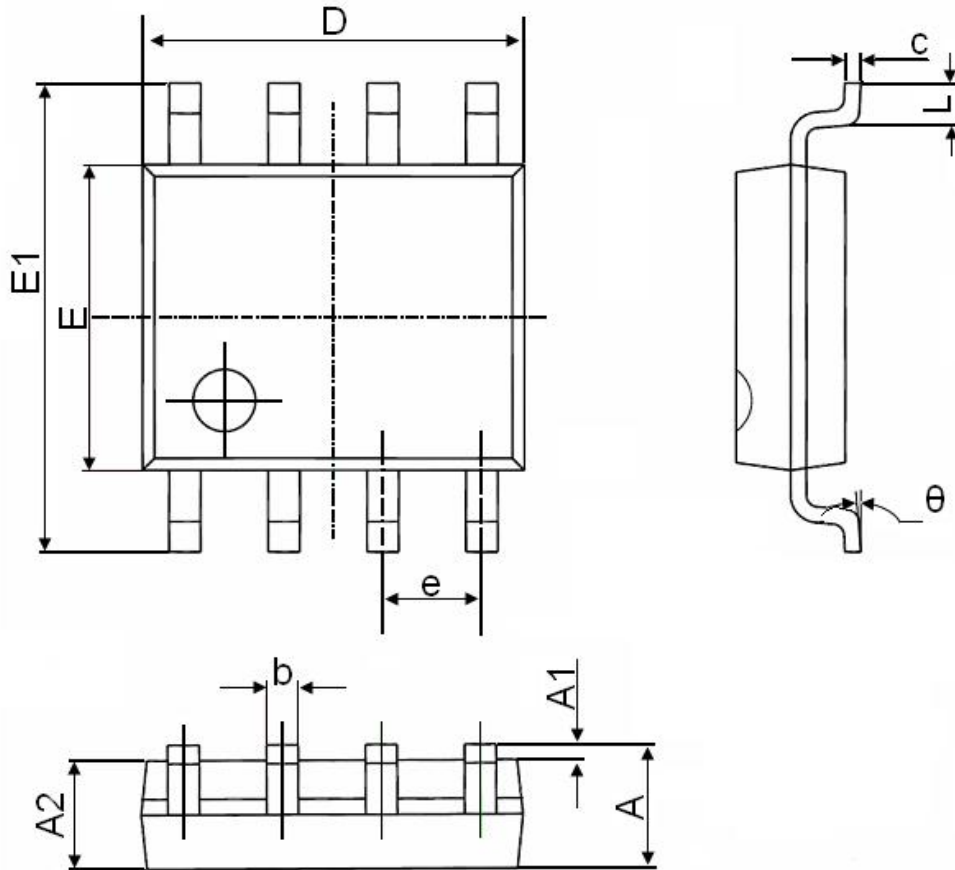


Figure 11 Normalized Maximum Transient Thermal Impedance



SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

## Attention

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